



Silicon Epitaxial Planar Diodes High Voltage Switching Diode

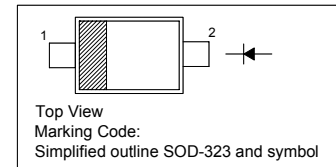
Features

- Fast switching speed
- Surface mount package ideally suited for automatic insertion

	BAV19WS	BAV20WS	BAV21WS
MARKING	JX	T2	T3

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

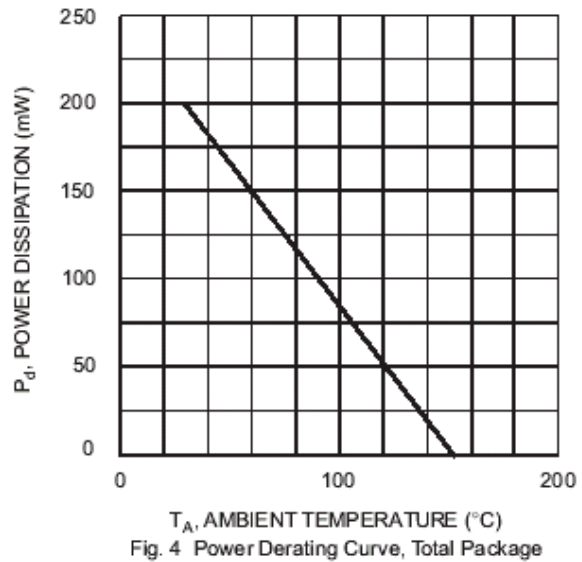
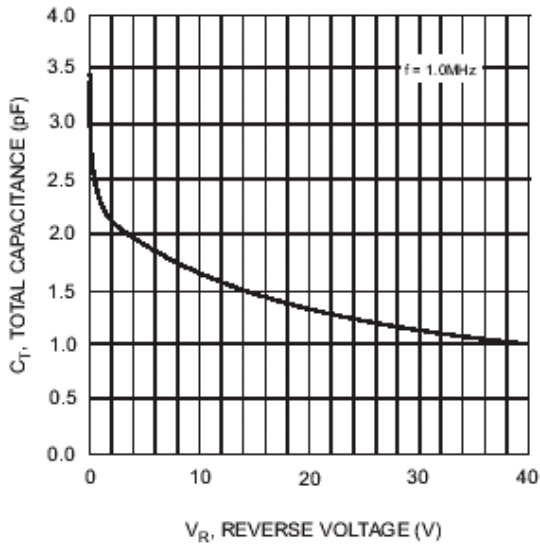
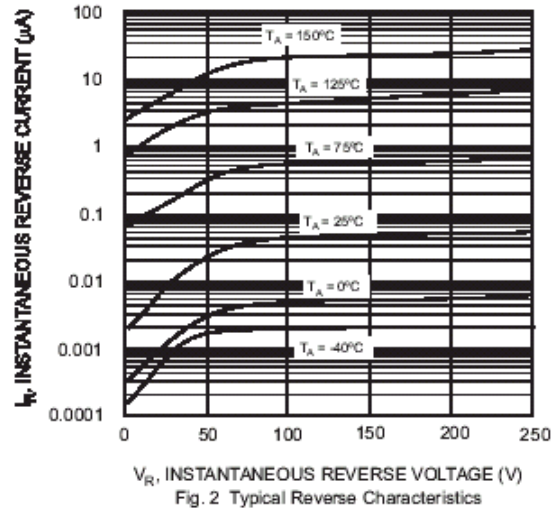
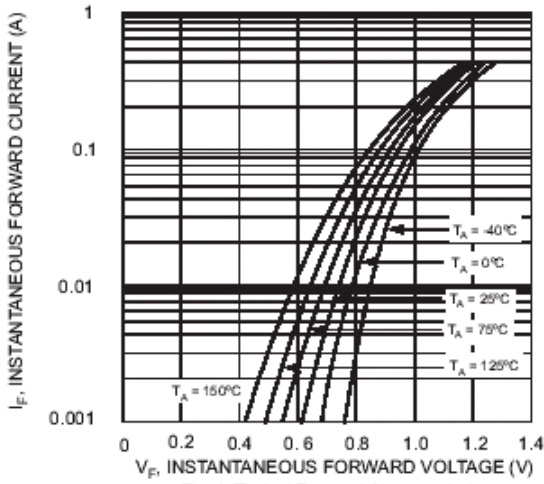


Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	BAV19WS BAV20WS BAV21WS	120 200 250	V
Reverse Voltage	BAV19WS BAV20WS BAV21WS	100 150 200	V
Average Rectified Forward Current	I _{F(AV)}	200	mA
Forward Continuous Current	I _{FM}	400	mA
Repetitive Peak Forward Current	I _{FRM}	625	mA
Non-Repetitive Peak Forward Surge Current	at t = 1 μs at t = 1 s	2.5 0.5	A
Power Dissipation	P _{tot}	200	mW
Operating and Storage Temperature Range	T _J , T _{stg}	- 65 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at I _R = 100 μA	BAV19WS BAV20WS BAV21WS	120 200 250	- - -	V
Reverse Current at V _R = 100 V at V _R = 150 V at V _R = 200 V	BAV19WS BAV20WS BAV21WS	- - -	100 100 100	nA
Forward Voltage at I _F = 100 mA at I _F = 200 mA	V _F	- -	1 1.25	V
Total Capacitance at V _R = 0, f = 1 MHz	C _T	-	5	pF
Reverse Recovery Time at I _F = I _R = 30 mA, I _{RR} = 0.1 X I _R , R _L = 100 Ω	t _{rr}	-	50	ns

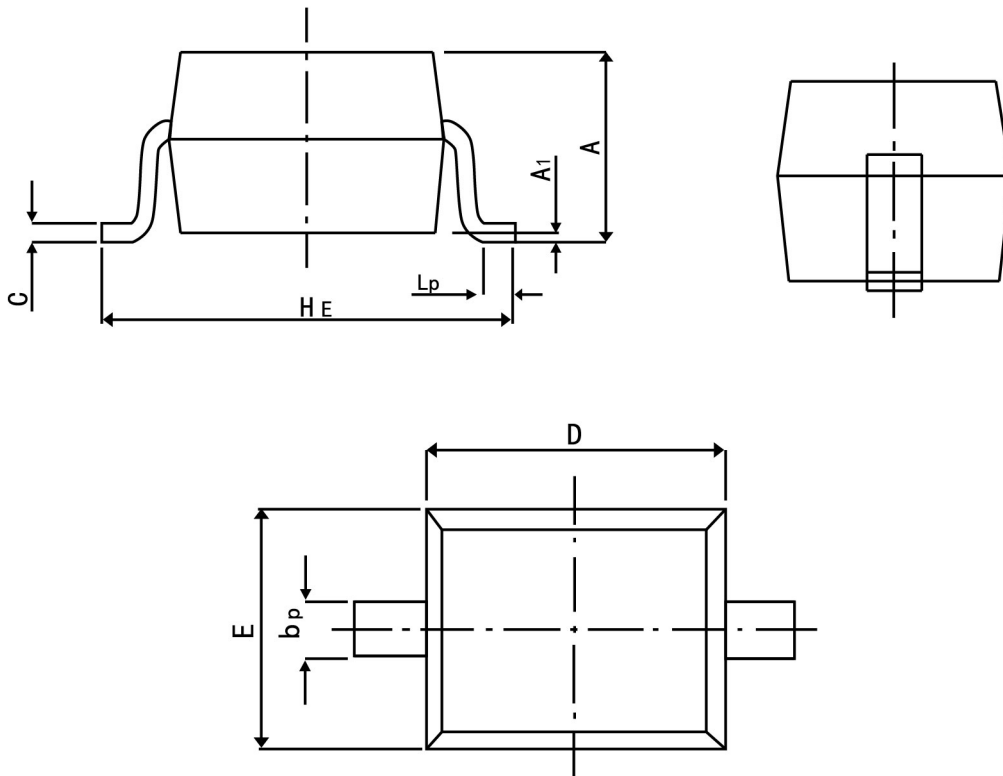




PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.20
bp	0.25	0.40
C	0.10	0.15
D	1.60	1.80
E	1.15	1.35
HE	2.30	2.80
A1	0.01	0.10
Lp	0.20	0.50